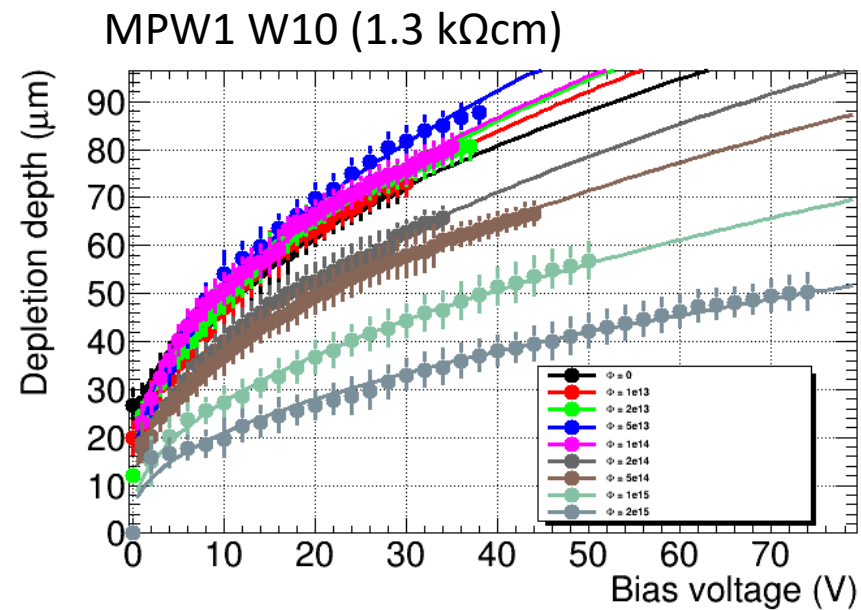
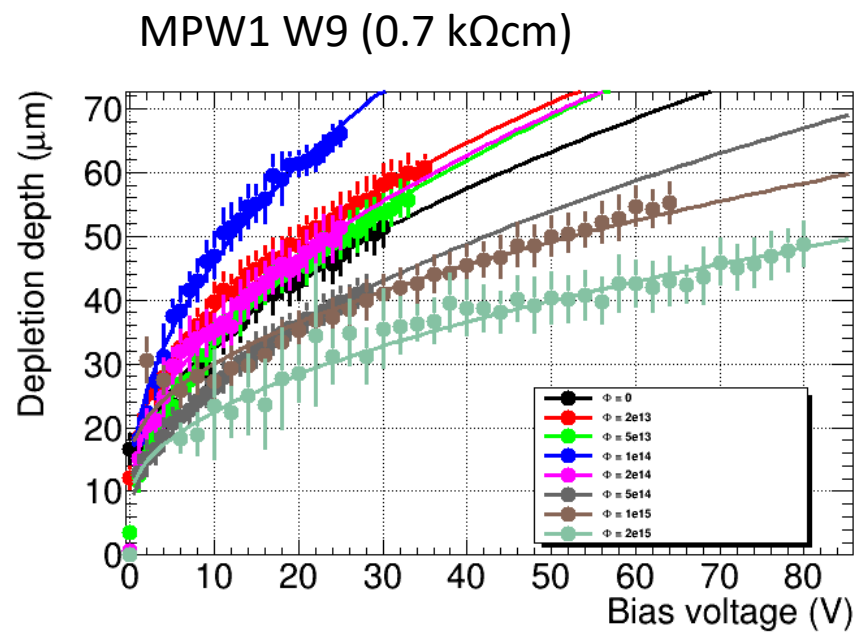
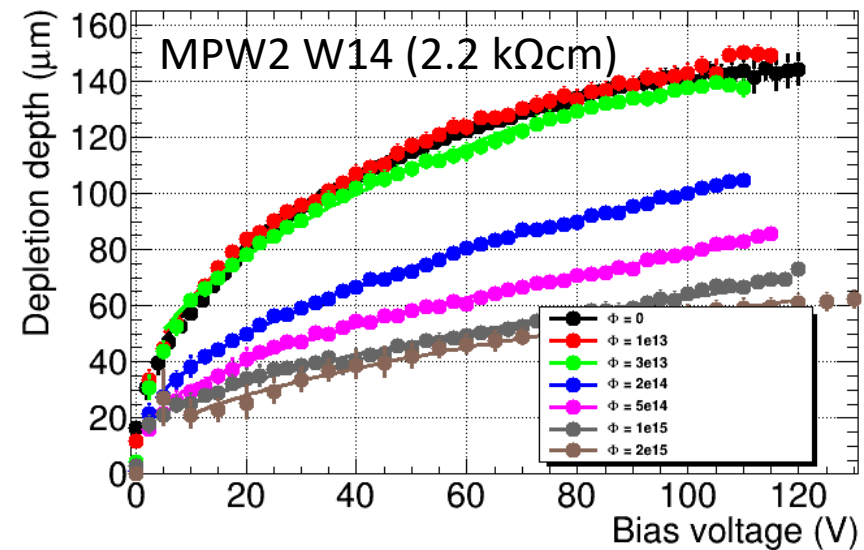
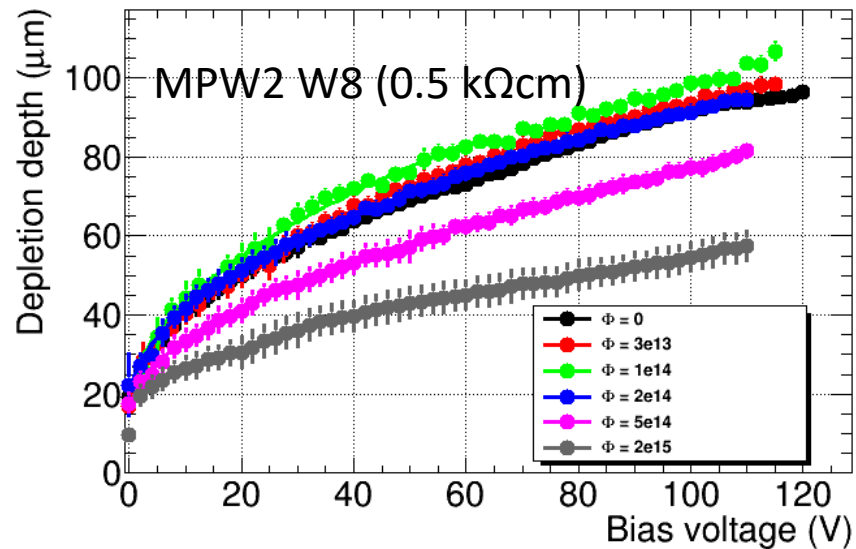
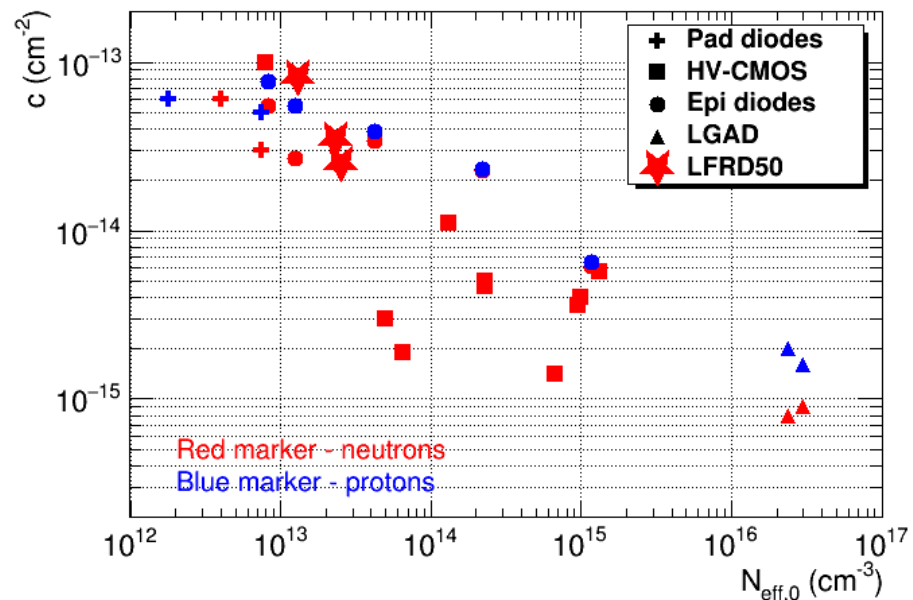
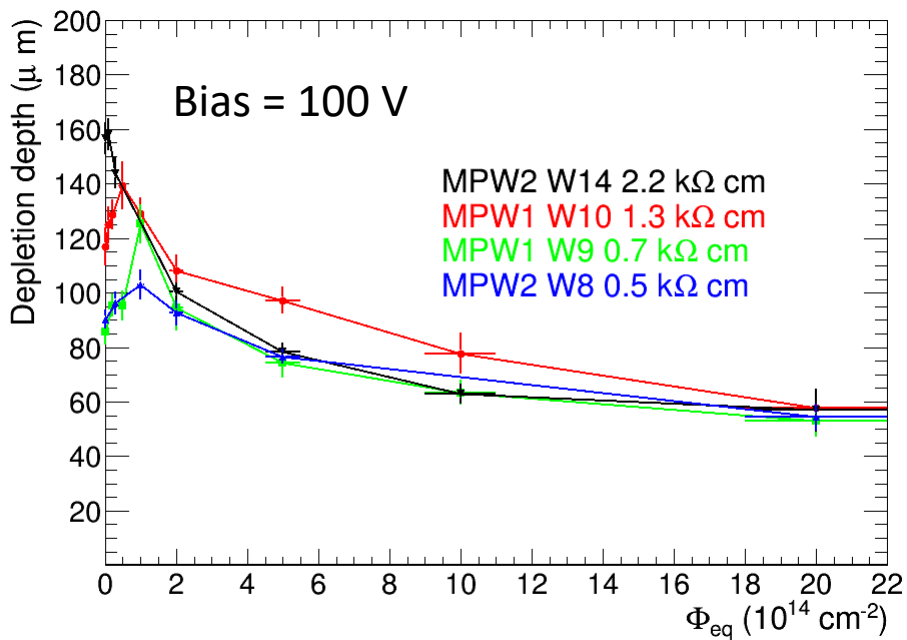
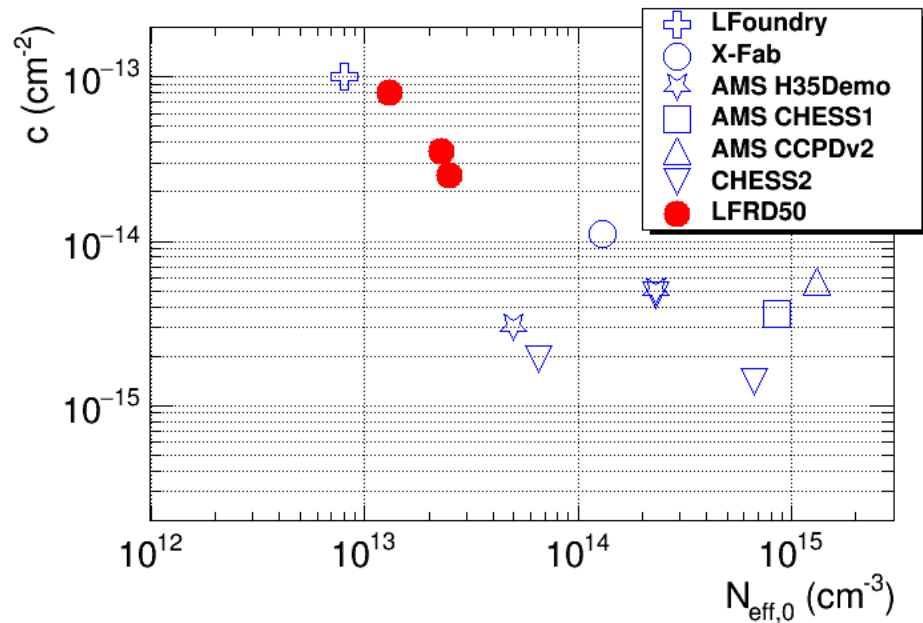
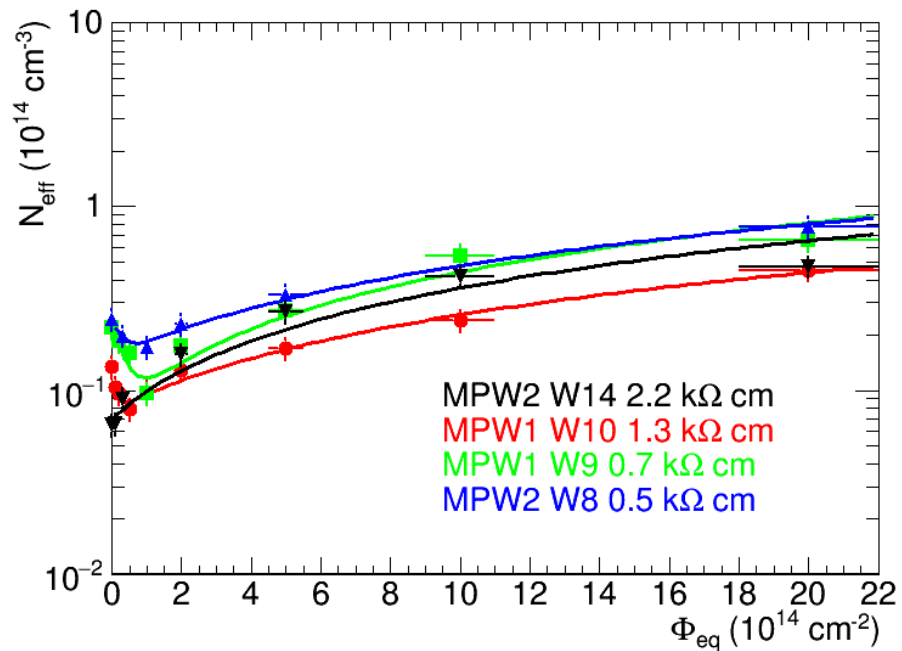
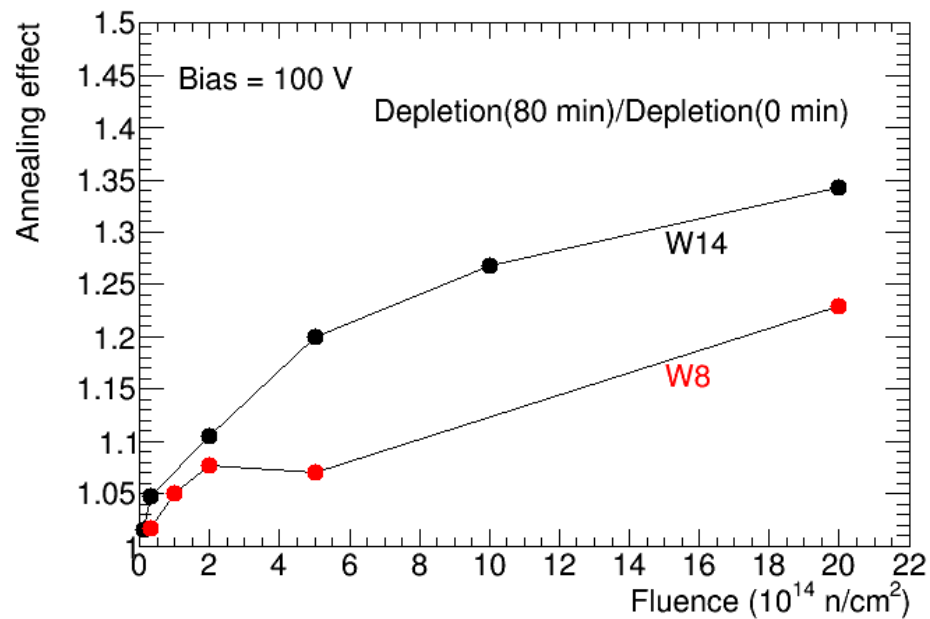
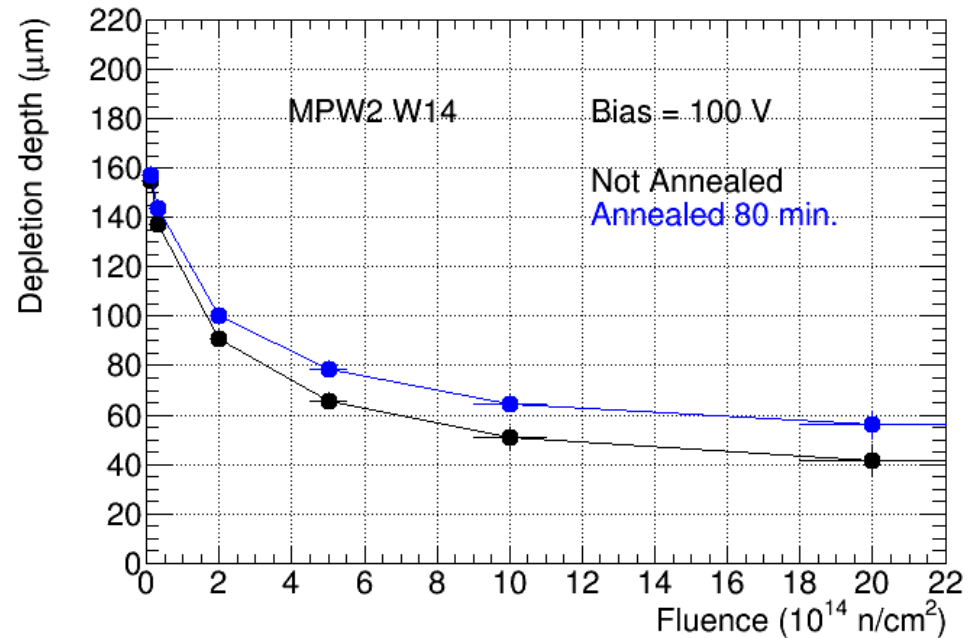
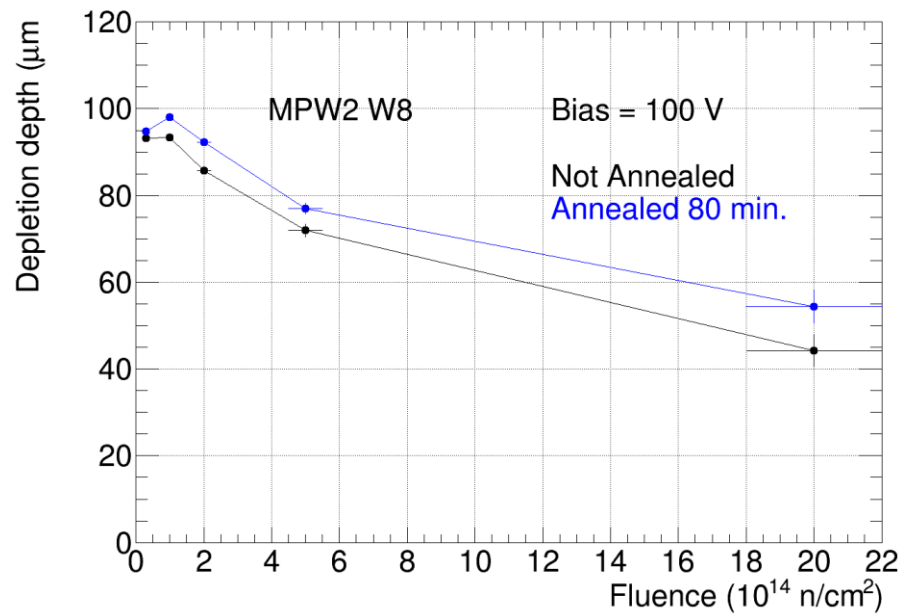


CMOS, E-TCT, IV







Current measured after annealing (80 mins at 60)

- dots: depletion depth d from $I = \alpha \cdot \Phi \cdot S \cdot d$
 $\alpha = 4E-17 \text{ Acm}^{-1}$
- lines: depletion depth from E-TCT

